DECLARATION (37 CFR 1.63) FOR UTILITY OR DESIGN APPLICATION USING AN APPLICATION DATA SHEET (37 CFR 1.76)

Electronic Version v11
Stylesheet Version v10

Title of Invention

METHOD OF MEASURING A GATE CHANNEL LENGTH OF A METAL-OXIDE SEMICONDUCTOR TRANSISTOR

As the below named inventors, we declare that:

This declaration is directed to the invention titled: "METHOD OF MEASURING A GATE CHANNEL LENGTH OF A METAL-OXIDE SEMICONDUCTOR TRANSISTOR"

We believe that we are the original and first inventors of the subject matter which is claimed and for which a patent is sought;

We have reviewed and understand the contents of the above-identified application, including the claims, as amended by any amendment specifically referred to above;

We acknowledge the duty to disclose to the United States Patent and Trademark Office all information known to us to be material to patentability as defined in 37 CFR 1.56, including for continuation-in-part applications, material information which became available between the filing date of the prior application and the national or PCT International filing date of the continuation-in-part application.

All statements made herein of own knowledge are true, all statements made herein on information and belief are believed to be true, and further that these statements were made with the knowledge that willful false statements and the like are punishable by fine or imprisonment, or both, under 18 U.S.C. 1001, and may jeopardize the validity of the application or any patent issuing thereon.

FULL NAME OF INVENTORS:

Inventor 1: Cheng-Tung Huang	Inventor
Signature :	Citizen of : TW
Inventor 2: Sheng-Hao Lin	Inventor
Signature :	Citizen of : TW
Inventor 3: Nien-Chung Li	Inventor

Signature :	Citizen of : TW	1
Inventor 4: Yi-Cheng Sheng	Inventor	
Signature :	Citizen of : TW	

COMBINED DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I hereby declare that:

I believe I am the sole (if only one name appears below), or joint (if more than one name appears), original and first inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled:

"METHOD OF MEASURING A GATE CHANNEL LENGTH OF A METAL-OXIDE SEMICONDUCTOR TRANSISTOR"

+	The specification for the above enti	tled invention is filed herewith.
	_ The specification for the above enti	tled invention was filed previously
with app	plication serial number:	Filing Date:
sŗ	I hereby state that I have reviewed and pecification, including the claims, as amended	d understand the contents of the above identified by any amendment referred to above.
I acknowledge the duty to disclose information which is material to the patentability of the invention disclosed in this application in accordance with Title 37, Code of Federal Regulations, Section 1.56 (a). I further acknowledge the duty in any continuation-in-part application to disclose to the Patent and Trademark Office all information known to be material to the patentability of the invention disclosed in this application, as defined in 1.56, which became available to me between the filing date of the prior application and the filing date of this application.		
	<u>PRIORI</u>	ΓΥ CLAIM
	There is no claim of priority	
+ Claim of priority is based on the following: Filing No. in Taiwan R.O.C.: 092109797		
11-11-11-11-11-11-11-11-11-11-11-11-11-	Filing date in Taiwan, R	
POWER OF ATTORNEY		
ар	pplication and to transact all related business i	oint the following attorneies to prosecute this in the Patent and Trademark Office:
	P.O. Box 506, Merrifield, Virginia 22116, U.S.A E-mail: winstonhsu@naipo.com.tw	

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DECLARATION

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment or both under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued hereon.

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